

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	2	"6680260".pn.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	84	(wafer) near10 (chamber) near26 (argon near10 pressure)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	16	(wafer) near10 (chamber) near26 (argon near10 pressure) near25 (temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	60	(wafer) near26 (argon near10 pressure) near25 (temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	1	(wafer) near26 (argon near10 pressure) near25 (predetermin\$3 near3 temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	0	(wafer) near26 (argon near10 pressure) near25 (pre-determin\$3 near3 temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	0	(wafer) near26 (argon near10 pressure) near25 (pre-determin\$3 near15 temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	9	(wafer) near26 (argon near10 pressure) near25 (heat\$3 near15 temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	53	(substrate) near26 (argon near10 pressure) near25 (heat\$3 near15 temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	2	(substrate) near26 (argon near10 pressure) near25 (heat\$3 near15 temperature) near25 (cool\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	2	(wafer) near26 (argon near10 pressure) near25 (heat\$3 near15 temperature) near25 (cool\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	12	(wafer) near26 (argon) near25 (heat\$3 near15 temperature) near25 (cool\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	17	(substrate) near26 (argon) near25 (heat\$3 near15 temperature) near25 (cool\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	61	(substrate) near26 (argon) near25 (heat\$3) near15 (cool\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	65	(wafer) near26 (argon) near25 (heat\$3) near15 (cool\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	169430 6	(cool\$3) (wafer or substrate) near15(celcius near per near second)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	169430 6	(cool\$3) (wafer or substrate) near15 (celcius near per near second)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
18	BRS	L18	169430 7	(cool\$3) (wafer or substrate) near15 (celsius near per near second)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L19	2	(cool\$3) near15 (wafer or substrate) near15 (celsius near per near second)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
20	BRS	L20	104	(cool\$3) near15 (wafer or substrate) near15 (celsius)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
21	BRS	L21	56	20 and (chamber)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
22	BRS	L22	43	20 and (chamber near25 pressure)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
23	BRS	L23	16	20 and (chamber near25 pressure near15 temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
24	BRS	L24	0	(cool\$3) near15 (argon or ar) near15 (wafer or substrate) near15 (celsius)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
25	BRS	L25	0	((argon or ar) near15 (wafer or substrate)) near15 (cool\$3 near10 celsius)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
26	BRS	L26	4	((argon or ar) near15 (wafer or substrate)) same (cool\$3 near10 celsius)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 20040171257 A1	Method for reducing free surface roughness of a semiconductor wafer
2			US 20030020096 A1	Method of producing a bonded wafer and the bonded wafer
3			US 20010030351 A1	Low temperature process for forming intermetal gap-filling insulating layers in silicon wafer integrated circuitry
4			US 6680260 B2	Method of producing a bonded wafer and the bonded wafer
5			US 6492682 B1	Method of producing a bonded wafer and the bonded wafer
6			US 6479881 B2	Low temperature process for forming intermetal gap-filling insulating layers in silicon wafer integrated circuitry
7			US 6413310 B1	Method for producing silicon single crystal wafer and silicon single crystal wafer
8			US 6391796 B1	Method for heat-treating silicon wafer and silicon wafer
9			US 6268274 B1	Low temperature process for forming inter-metal gap-filling insulating layers in silicon wafer integrated circuitry
10			US 5778968 A	Method for heating or cooling wafers
11			US 4756815 A	Wafer coating system
12			JP 411135514 A	SILICON WAFER AND ITS HEAT TREATMENT METHOD